
**ELECTROTHERMAL ANALYSIS
OF
VLSI SYSTEMS**

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Contents

List of Figures	ix
List of Tables	xv
Preface	xvii
Acknowledgments	xxi

Part I THE BUILDING BLOCKS

1. INTRODUCTION	3
1.1. Electrothermal Phenomena in VLSI Systems	4
1.2. Introduction to Electrothermal Simulation	5
1.2.1 Overview of Electrothermal Simulation for ICs	6
1.3. ILLIADS-T: An Electrothermal Simulator for VLSI Systems	12
1.4. Overview of this Book	15
2. POWER ANALYSIS FOR CMOS CIRCUITS	21
2.1. Introduction	21
2.2. Sources of Power Consumption in CMOS Technology	21
2.2.1 Dynamic Power	22
2.2.2 Internal Power	23
2.2.3 Short-circuit Power	24
2.2.4 Leakage Power	25
2.3. Power Analysis Overview	28
2.4. Introduction to Power Analysis Techniques	29
2.4.1 Deterministic Power Analysis	29
2.4.2 Probabilistic Power Analysis	30
2.4.3 Statistical Power Analysis	33
2.4.4 Power Analysis for Sequential Circuits	37
2.5. Summary	39
3. TEMPERATURE-DEPENDENT MOS DEVICE MODELING	45
3.1. Introduction	45
3.2. Temperature-dependent Device Physics and Modeling	46

3.2.1	Temperature-dependent Threshold Voltage	46
3.2.2	Temperature-dependent Carrier Mobility	47
3.3.	Temperature-dependent BSIM Model for SPICE Simulation	48
3.4.	Regionwise Quadratic (RWQ) Model	51
3.4.1	Temperature-dependent Mobility Modeling	53
3.4.2	$\mu_0(T)$ Extraction for RWQ Modeling	54
3.4.3	Mobility and RWQ Fitting Examples	54
3.5.	Summary	57
4.	THERMAL SIMULATION FOR VLSI SYSTEMS	61
4.1.	Introduction	61
4.2.	Substrate/Package Modeling: An Overview	64
4.3.	Formulation of Thermal Analysis	65
4.3.1	Fast Thermal Analysis	65
4.3.2	Numerical Approach	72
4.3.3	Analytical Approach	79
4.3.4	Discussion	82
4.4.	Package Simulation	83
4.4.1	Modeling of the Convective Boundaries	83
4.4.2	Modeling of Heat Flow Paths	84
4.5.	Summary	88
5.	FAST-TIMING ELECTROTHERMAL SIMULATION	95
5.1.	Introduction	95
5.2.	ILLIADS: A Fast Timing Simulator	96
5.2.1	Primitive Formation and Solutions	96
5.2.2	Simulation Strategies	98
5.2.3	Power Estimation using ILLIADS	101
5.3.	Incremental Electrothermal Simulation in ILLIADS-T	101
5.4.	Tester Chip Design and Calibration	103
5.5.	Verification of ILLIADS-T	105
5.6.	ILLIADS-T Simulation Examples	112
5.7.	Summary	116

Part II THE APPLICATIONS

6.	TEMPERATURE-DEPENDENT ELECTROMIGRATION RELIABILITY	121
6.1.	Motivation	121
6.2.	Electromigration (EM) Physics	122
6.2.1	EM Lifetime Dependence on Current Density	123
6.2.2	EM Lifetime Dependence on Current Waveforms	124
6.2.3	EM Lifetime Dependence on Interconnect Width and Length	127
6.2.4	EM Model Used in the Book	129
6.3.	EM Simulation: An Overview	129

6.4.	ITEM: A Temperature-dependent EM Diagnosis Tool	133
6.4.1	Interconnect Temperature Estimation	133
6.4.2	Analytical Model of Interconnect Thermal System	135
6.4.3	Lumped Model of Interconnect Thermal System	136
6.4.4	iTEM Simulation Examples	143
6.5.	Summary	148
7.	TEMPERATURE-DRIVEN CELL PLACEMENT	157
7.1.	Introduction	157
7.2.	Overview	157
7.3.	Substrate Temperature Calculation	160
7.4.	Compact Substrate Thermal Modeling	161
7.4.1	Transfer Thermal Resistance Matrix	161
7.4.2	Admittance Matrix Reduction	163
7.4.3	Runtime Efficiency of Compact Thermal Modeling	164
7.5.	Thermal Placement Algorithms	165
7.5.1	Standard Cell Thermal Placement	165
7.5.2	Macrocell Thermal Placement	168
7.6.	Simulation Examples	169
7.7.	Summary	172
8.	TEMPERATURE-DRIVEN POWER AND TIMING ANALYSIS	181
8.1.	Introduction	181
8.2.	Timing Analysis Overview	182
8.2.1	Dynamic Timing Analysis	182
8.2.2	Static Timing Analysis	183
8.2.3	Delay Modeling	190
8.3.	Statistical Power Density Estimation	191
8.4.	Monte-Carlo Power-Temperature Iteration Scheme	192
8.5.	Temperature-dependent Gate and RC Delays	194
8.6.	Simulation Examples	194
8.7.	Summary	199

List of Figures

1.1	Applications of electrothermal CAD tools.	5
1.2	Elements of electrothermal simulations.	6
1.3	Electrothermal simulation procedure in [1].	7
1.4	(a) An RC circuit example, (b) the dc circuit for the first-moment generation, and (c) the dc circuit for finding the second moment.	10
1.5	The integrator circuit used to implement the solution of the 3-D heat diffusion equation.	11
1.6	Flowchart of ILLIADS-T electrothermal simulation.	13
2.1	Illustration of dynamic power consumption in a CMOS inverter.	22
2.2	Charging and discharging of an internal node of 2-input NOR gate.	23
2.3	Short-circuit power for inverter with large load.	25
2.4	Short-circuit power for inverter with small load.	26
2.5	Leakage current at reversed-biased diode junction.	26
2.6	Subthreshold leakage current.	27
2.7	(a) Logic circuit without reconvergent fan-out, and (b) Logic circuit with reconvergent fan-out.	32
2.8	A standard statistical power estimation flow.	34
2.9	Relationship between F , a , and the confidence level.	35
2.10	A generic sequential circuit.	37
3.1	BSIM sensitive parameter subset approach.	50
3.2	BSIM parameter value update using temperature coefficients.	52
3.3	Regionwise partition of the (V_{DS} , V_{GSE}) plane.	53
3.4	Fitted $\mu_0(T)$ vs. extracted $\mu_0(T)$.	55
3.5	NMOSFET: (a) RWQ fitting result at 27 °C, and (b) RWQ fitting result at 100 °C with mobility optimization.	55

3.6	PMOSFET: (a) RWQ fitting result at 27 °C, and (b) RWQ fitting result at 100°C with mobility optimization.	56
3.7	Figure	56
4.1	A thermal simulation framework [2].	63
4.2	Illustration of effective heat transfer macromodeling.	64
4.3	Method of images.	66
4.4	Error function approximation.	67
4.5	Transformation 1: Constrain the observation point to the first quadrant.	68
4.6	Transformation 2: Constrain t_{a1} to be larger than t_{b1} .	69
4.7	An FTA example.	70
4.8	Chip structure and heat source locations.	71
4.9	(a) Top view of the solid containing heat sources, and (b) 3-D view of grid point (i, j, k).	74
4.10	(a) Analogous thermal circuit to Fig. 4.9(a), and (b) thermal conductances from (i, j, k) to adjacent grids.	74
4.11	Analogy between thermal and electrical circuits.	75
4.12	(a) Top view of a part of the chip comprised of composite materials, and (b) 3-D view of grid point (i, j, k).	76
4.13	(a) Analogous thermal circuit to Fig. 4.12(a), and (b) thermal conductances from (i, j, k) to adjacent grids.	77
4.14	Equivalent thermal circuit at the convective boundary.	78
4.15	Speedup of FTA over numerical method.	83
4.16	Layout of the solid containing three heat sources.	84
4.17	Temperature profiles along the x direction at $y = 500$ μm for three different h^e values.	85
4.18	Unit-level layout of a high-performance chip.	85
4.19	Cross-sectional view of a flip-chip package.	86
4.20	Equivalent thermal circuit of the flip-chip package.	87
4.21	Method to determine the thermal resistances for heat flowing through the carrier aside to the lids.	87
4.22	On-chip temperature contour for the first experiment.	88
4.23	On-chip temperature contour for the second experiment.	89
4.24	On-chip temperature contour for the third experiment.	89
5.1	General MOS circuit primitive used in ILLIADS.	97
5.2	Illustrations of SCC formation and topological sort: (a) the original circuit. (b) the digraph representation, and (c) the condensed digraph after topological sort.	99
5.3	Example of transistor merging and internal node elimination.	100
5.4	Primitive mapping for the circuit shown in Fig. 5.3 after the transistor merging process.	100

5.5	DCCB power calculation using ILLIADS.	101
5.6	Convergence plot for power and temperature.	102
5.7	Illustration of incremental latency: the nominal waveforms are shown in solid lines, while the perturbed waveforms are in dashed lines.	103
5.8	Microphotograph of the tester chip; long blocks are Rosc 149s and short blocks are Rosc3s.	104
5.9	Four-terminal configuration for diode measurement.	105
5.10	Diode calibration example (D1).	106
5.11	Simulated temperature profile for Expt. 2.	107
5.12	Simulated temperature profile for Expt. 1.	107
5.13	Comparison between simulated and measured temperatures for D1.	108
5.14	Comparison between simulated and measured temperatures for D2.	108
5.15	Comparison between simulated and measured temperatures for D3.	109
5.16	(a) Measured and (b) simulated waveforms for Expt. 8.	109
5.17	(a) Measured and (b) simulated waveforms for Expt. 7.	110
5.18	(a) Measured and (b) simulated waveforms for Expt. 5	110
5.19	(a) Measured and (b) simulated waveforms for Expt. 1.	111
5.20	Layout of the I0-bit negative adder.	112
5.21	Layout of the simulated chip.	113
5.22	Packaging structure used in the simulation example.	114
5.23	Output waveforms of the I0-bit negative adder.	115
6.1	The temperature effect on electromigration reliability.	122
6.2	An example of a bidirectional pulsed current density waveform.	127
6.3	Electromigration MTF as a function of interconnect width [14].	127
6.4	Microstructure of the interconnects.	128
6.5	Electromigration MTF as a function of interconnect length.	129
6.6	SPIDER [19] for the simulation of interconnect reliability.	130
6.7	CURRENT representation of a 2-input NAND gate.	131
6.8	A hierarchical environment for interconnect EM reliability diagnosis.	132
6.9	Simulation flowchart of iTEM.	134
6.10	The interconnect on insulator structure.	135

6.11	AT is a function of metal current density. The following parameters values are used to generate the data: $t_i = 2 \text{ } \mu\text{m}$, $t = 0.5 \text{ } \mu\text{m}$, $w = 2 \text{ } \mu\text{m}$, $\rho\sigma = 3.6 \times 10^{-6} \text{ } \Omega\text{-cm}$, $\beta = 4.04 \times 10^{-3} \text{ K}^{-1}$, $K_i = 1.835 \text{ W}/(\text{K}\cdot\text{m})$, and $T_s = 300 \text{ K}$.	137
6.12	(a) Interconnect with contacts to substrate, and (b) the corresponding temperature distribution from 3-D thermal simulation. Note that the interconnect temperature is reduced near the contacts and bond pads.	138
6.13	A lumped model of the interconnect thermal system.	139
6.14	A right-angle bend conductor.	140
6.15	A lumped model of the interconnect thermal system near a via.	141
6.16	(a) Simulated interconnect structure with four contacts to substrate. (b) Comparison of the thermal simulation results using lumped thermal model and 3-D simulation.	142
6.17	(a) Simulated multi-layered interconnect structure. (b) Comparison of thermal simulation results using lumped thermal model and 3-D simulation.	143
6.18	Procedure of the interconnect temperature estimator.	144
6.19	Example of partitioning the interconnect layout in the interconnect temperature estimator.	144
6.20	The lumped thermal model for a transistor with multiple contacts.	145
6.21	Strategies for grouping contacts that are close to each other.	145
6.22	Simulation results of multiple contacts which are close to each other.	146
6.23	A layout of 10-bit negative adder.	146
6.24	The power/ground bus layout of 10-bit negative adder.	147
6.25	iTEM simulation result of the 10-bit negative adder. The number marked is the predicted electromigration MTF in hours.	147
6.26	The power and ground bus layouts of the 2-D discrete cosine transformation chip.	148
6.27	iTEM simulation result of the 2-D discrete cosine transformation chip. The number marked is the predicted electromigration MTF in hours.	149
7.1(a)	Optimal heat distribution for a design with a core size $12\text{mm} \times 12\text{mm}$. The power density of the fixed cell near the lower-right corner of the layout is lower than the chip average.	158

7.1(b)	Optimal temperature distribution resulting from the heat distribution in Fig. 7.1(a).	159
7.2	Block diagram of the thermal placement algorithm.	165
7.3	Revised simulated annealing algorithm for standard cell thermal placement.	167
7.4	Revised simulated annealing algorithm for macrocell thermal placement.	169
7.5(a)	Temperature profiles of benchmark <i>ami49</i> without thermal placement. The ambient temperature is assumed to be zero.	172
7.5(b)	Temperature profiles of benchmark <i>ami49</i> with thermal placement. The ambient temperature is assumed to be zero.	173
7.6	Histograms of on-chip temperatures of <i>ami33</i> (a) before and (b) after thermal placement.	174
7.7	Histograms of on-chip temperatures of <i>ami49</i> (a) before and (b) after thermal placement.	174
7.8	Histograms of on-chip temperatures of <i>biomed</i> (a) before and (b) after thermal placement.	175
7.9	Histograms of on-chip temperatures of <i>primary1</i> (a) before and (b) after thermal placement.	175
7.10	Histograms of on-chip temperatures of <i>primary2</i> (a) before and (b) after thermal placement.	176
7.11	Histograms of on-chip temperatures of <i>sp1</i> (a) before and (b) after thermal placement.	176
7.12	Histograms of on-chip temperatures of <i>struct</i> (a) before and (b) after thermal placement.	177
7.13	Histograms of on-chip temperatures of <i>industry1</i> (a) before and (b) after thermal placement.	177
8.1	Relations between power, temperature, and timing.	182
8.2	Block diagram of static timing analysis.	184
8.3	An example circuit diagram.	185
8.4	Arrival time propagation in block-oriented analysis.	186
8.5	Required arrival time propagation in block-oriented analysis.	188
8.6	Slack calculation in block-oriented analysis.	189
8.7	A false path example.	189
8.8	Monte-Carlo power and temperature iteration scheme.	193
8.9	Example of a distributed RC tree.	195
8.10	Example of an equivalent π model.	195
8.11	Thermal boundary conditions for temperature-dependent timing simulation.	196

- 8.12 The simulated temperature profile and the gate distribution of the longest path in C6288: The solid lines are the isothermal temperature contour and the small diamonds are the on-chip locations of gates in the longest path.

List of Tables

1.1	Trends of future microprocessor characteristics (ref: 1997 NTRS). Here the on-chip temperature is calculated assuming an ambient temperature of 75 °C.	4
3.1	BSIM sensitive parameters	50
4.1	Error function approximations.	68
4.2	Eight cases under six constraints.	69
4.3	Violation rate by using the FTA method.	71
4.4	Definition of the symbols in Fig. 4.20.	86
5.1	Activation status of Rosc3s.	106
5.2	ILLIADS-T simulation results of the tester chip.	111
5.3	ILLIADS-T simulation results.	113
5.4	Packaging parameters for thermal simulation.	114
5.5	ILLIADS-T simulation results.	115
6.1	Simulation results of iTEM.	150
7.1	Standard cell thermal placement simulation results.	170
7.2	Macrocell thermal placement simulation results.	170
8.1	The ISCAS85 benchmark circuits.	196
8.2	Simulation results with dynamic timing analysis.	197
8.3	Simulation results with static timing analysis.	198

Preface

With increasing complexity of VLSI chips, the task of developing state-of-the-art VLSI systems has become a highly challenging multidisciplinary task. Although in early days of MOS technology, silicon compilation looked promising, it has become difficult to fully automate the entire design flow from high-level design to mask generation due to many difficult physical design problems, including timing closure, power constraint, crosstalk, signal integrity, testability and reliability issues. In particular, the conventional practice of treating reliability qualification as a backend process has become no longer acceptable in view of excessive cost for design iterations. Attempts are under way to include reliability verification in the design flow so that expensive design iterations due to reliability problems can be avoided.

With foresight Semiconductor Research Corporation has provided strong support on our research of “design for reliability” at the University of Illinois at Urbana-Champaign for over a decade. New models and CAD capabilities have been developed and transferred to industry to address some of the serious reliability problems such as electromigration (EM) in metallic interconnects and electrostatic discharge (ESD) damages to I/O pads. With increasing concerns for on-chip power dissipation due to high packing density and high-frequency operation, electrothermal analysis has become critically important for accurate assessment of thermally activated device and circuit failures, and for timing analysis.

In this book we have attempted to provide in-depth coverage of important subjects required for electrothermal analysis of MOS VLSI circuits in an orderly manner. The underlying principles of circuit models and simulation algorithms in reliability CAD tools such as ILLIADS-T and iTEM are described in detail. For verification of design tool capability, chip design and bench test results are presented for electrothermal analysis of ring oscillators operating under digitally controlled thermal environment. We also present a “thermally skewed timing failure” phenomenon with detailed simulation result. This subject has

not been discussed in any literature to our best knowledge, but such failures have been noticed by practicing VLSI design engineers.

It is our sincere desire that readers will find the contents of this book useful for practice and also for furtherance of research in this challenging field.

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Foreword

Continuing increases in the levels of circuit integration and concomitant increases in performance are sustaining the trend of increasing power dissipation in VLSI systems. A consequence is that the impact of temperature on the successful operation and reliability of devices must be comprehended during the design process. For the past decade, the authors have led an effort to provide a framework, accompanied by tools, for the electrothermal analysis and design of integrated circuits and systems. This is a challenging field driven by the enormous complexity of integrated circuits and by the need for tractable, predictive, and executable models of electrical and thermal interaction physics.

This text provides a comprehensive formulation of the electrothermal analysis problem beginning with a summary of the sources of power dissipation in CMOS circuits and followed by a formulation of the effect of temperature on MOS devices. A general framework for thermal simulation of integrated circuits and packages is presented and then the fast timing electrothermal simulator, ILLIADS-T, is described. Applications include the study of temperature dependent electromigration reliability, captured in the simulator iTEM, and the placement of cells so as to mitigate temperature effects. The text concludes with the description of a methodology to predict the effects of temperature on the timing of integrated circuits.

The tools and methods described herein are finding widespread use in industrial applications by SRC members. We at the SRC are pleased to acknowledge the important contributions that have been made by the authors and expect that readers who are involved in electrothermal modeling will find the integrated perspective of this text to be very useful.

Dr. Ralph K. Cavin, Vice President
Semiconductor Research Corporation
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